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→ 10/806612

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Complete If Known	
		Application Number	10/806612
		Filing Date	Concurrently Herewith
		First Named Inventor	Joseph J. Nahas
		Group Art Unit	
Examiner Name			
Sheet 1 of 1	Attorney Docket Number	SC13159TC	

U. S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number -Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant - Passages or Relevant Figures Appear
JO	AA	5,867,405	02/02/1999	Jiang <i>et al.</i>	
JO	AB	2002/0141232 A1	10/03/2002	Saito <i>et al.</i>	
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FOREIGN PATENT DOCUMENTS						
Examine Initials*	Cite No. ¹	Foreign Patent Document Country Code ² Number ³ Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁷
JO	AC	Bae <i>et al.</i> , "Fabrication and Thermal-Chemical Stability of Magnetoresistive Random-Access Memory Cells Using α -Fe ₂ O ₃ Bottom Spin Values," <i>IEEE Transactions on Magnetics</i> , Vol. 37, No. 6, November 2001, pp. 3960-3968.	
JO	AD	Cheung, "Direct Charging Charge Device Model Testing of Magnetoresistive Recording Heads," <i>EOS/ESD Symposium</i> 97-398, 1997, pp. 398-404.	
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JO	AI	A. Maxim <i>et al.</i> , "A New Analog Behavioral SPICE Macromodel of Magnetic Components," <i>IEEE International Symposium on Industrial Electronics</i> , Guimarães, Portugal, University of Minho, July 7-11, 1997, pp. 183-188, Vol. 2 of 3.	
JO	AJ	A. Maxim <i>et al.</i> , "A Novel Behavioral Method of SPICE Macromodeling of Magnetic Components Including the Temperature and Frequency Dependencies," <i>IEEE Power Electronics Conference</i> , 1998, pp. 393-399.	
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JO	AM	A. Wallash <i>et al.</i> , "ESD Evaluation of Tunneling Magnetoresistive (TMR) Devices," <i>EOS/ESD Symposium</i> , 2000, pp. 470-474.	
JO	AN	U.S. Patent Application 10/302,203 filed November 22, 2002, entitled "Method and Apparatus for Simulating a Magnetoresistive Random Access Memory (MRAM)", assignee same as assignee hereof.	

Examiner Signature	Date Considered	12/12/05
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